

INFORMATION DISCLOSURE CITATION
(Use several sheets if necessary)

ATTY DOCKET NO.
BREV 12370 CON 2

SERIAL NO. 777516

ASPAR ET AL

FILING

2/6/01

GROUP

2823

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
Dae	4,704,302	11/3/87	Bruel et al			
	5,234,535	8/10/93	NBeyer et al			
	5,494,835	2/27/96	Bruel			
	5,804,086	9/8/98	Bruel			
	5,817,368	10/6/98	Hashimoto			
	5,863,830	1/26/99	Bruel et al			
	5,897,331	4/27/99	Sopori			
	5,633,174	5/27/97	Li			
Y	5,250,446	10/5/93	Osowa et al			

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	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
Dae	WO95/20824	8/3/95	PCT			✓	
	EP 0703 609	3/27/96	EPO			✓	
	0 660 140	6/28/95	EPO			✓	
	GB 2 211 991	7/12/89	UK				

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Dae		EerNisse, E.P. et al, "Role of integrated lateral stress in surface deformation of He-implanted surfaces," Journal of Applied Physics, Vol 48, No 1, January 1997, pp 9-17
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D.M. Courts

DATE CONSIDERED

12-21-07

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INFORMATION DISCLOSURE CITATION
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Docket Number (Optional)
BREV 12370 CON

Application Number
777516

Applicant(s)
Aspar et al

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2/6/01

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2823

*EXAMINER INITIAL	OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)
Dmc	Roth, J., "Blistering and bubble formation," Inst. Phys. Conf. Ser., No. 28, 1976, pp 280-293
	Ligeon, E. et al, "Hydrogen Implantation in Silicon Between 1.5 and 60 KeV," Radiation Effects, Col. 27, 1976, pp 129-137
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	Ascheron, C. et al, "The Effect of Hydrogen Implantation Induced Stress on GaP Single Crystals, Nuclear Instruments & Methods in Physics Research, B28, 1987, pp 350-359
	Bruehl, Michel, "Application of hydrogen ion beams to Silicon on Insulator material technology", Nuclear Instruments and Methods in Physics Research, B108, 1996, pp 313-319
	Auberton-Herve, A.J. et al, "SOI Materials for ULSI Applications", Semiconductor International, October 1995, 5 pps.
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D. M. COVER

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FORM PTO-1449	SERIAL NO.	CASE NO. BREV 12370 CON 2
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	FILING DATE	GROUP ART UNIT
(use several sheets if necessary)	APPLICANT(S): Aspar et al.	

REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

U.S. PATENTS

<u>PATENT NO.</u>	<u>INVENTOR</u>	<u>ISSUE DATE</u>
4,179,324	12/18/79	Kirkpatrick
5,110,748	5/5/92	Sarma
5,310,446	5/10/94	Konishi et al.
5,661,333	8/26/97	Bruehl et al.

FOREIGN PATENTS

<u>DOCUMENT NO.</u>	<u>COUNTRY</u>	<u>DATE</u>
2725074	France	March 29, 1996
0355913	EPO	February 28, 1990
0504714	EPO	September 23, 1992

OTHER PUBLICATIONS

Silicon-On-Insulator, European Semiconductor, March, 1997, pages 17 and 18

Aspar et al., SMART-CUT®: The basic fabrication process for UNIBOND® SOI wafers, SEMI 1996, pp. 37-46

Klem et al., Characteristics of lift-off fabricated AlGaAs/InGaAs single-strained quantum well structures on glass and silicon substrates, *Inst. Phys. Conf.*, Ser. No 96: Chapter 6, pp. 387-392

Hamaguchi et al., Device Layer Transfer Technique using Chemi-Mechanical Polishing, *Japanese Journal of Applied Physics*, 23(1984), Oct., No. 10, Part 2, Tokyo, Japan, pp. L815-L817

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D. A. Courts

12-21-01

FORM PTO-1449	SERIAL NO. 777516	CASE NO. BREV 12370 CON 2
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	FILING DATE 2/6/01	GROUP ART UNIT 2823
(use several sheets if necessary)	APPLICANT(S): Aspar et al.	

REFERENCE DESIGNATION U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS/ SUBCLASS	FILING DATE
Dme	A1	4,179,324	12/18/79	Kirkpatrick	156/230	11/28/77
	A2	5,110,748	5/5/92	Sarma	437/51	7/22/91
	A3	5,310,446	5/10/94	Konishi et al.	117/58	7/13/92
	A4	5,661,333	8/26/97	Bruel et al.	257/618	1/25/95
	A5					
	A6					
	A7					
	A8					

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS/ SUBCLASS	TRANSLATION YES NO
Dme	A9	2725074	3/29/96	France		X
	A10	0355913	2/28/90	EPO		X
	A11	0504714	9/23/92	EPO		X

EXAMINER INITIAL	OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)	
Dme	A12	Silicon-On-Insulator, <i>European Semiconductor</i> , March, 1997, pages 17 and 18
	A13	Aspar et al., SMART-CUT®: The basic fabrication process for UNIBOND® SOI wafers, <i>SEMI</i> 1996, pp. 37-46
	A14	Klem et al., Characteristics of lift-off fabricated AlGaAs/InGaAs single-strained quantum well structures on glass and silicon substrates, <i>Inst. Phys. Conf., Ser. No 96: Chapter 6</i> , pp. 387-392
	A15	Hamaguchi et al., Device Layer Transfer Technique using Chemi-Mechanical Polishing, <i>Japanese Journal of Applied Physics</i> , 23(1984), Oct., No. 10, Part 2, Tokyo, Japan, pp. L815-L817
	A16	Haisma et al., Silicon-on-Insulator Wafer Bonding-Wafer Thinning Technological Evaluations, <i>Japanese Journal of Applied Physics</i> , 28(1989), Aug., No. 8, Part 1, Tokyo, Japan, pp. 1426-1443

EXAMINER D.M. Collins	DATE CONSIDERED 12-21-01
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*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
Dme	4,931,405	06/05/1990	KAMIJO ET AL	437	12	
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						YES	NO
Dme	53-104156	09/11/1978	JAPAN	H01L	21/322		✓
Dme	59-54217	03/29/1984	JAPAN	H01L	21/20		✓

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Applicant(s) ASPAR ET AL		
Filing Date 2/6/01	Group Art Unit 2823	

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DMC	ERROL P. EERNISSE, COMPACTION OF ION-IMPLANTED FUSED SILICA, 1973
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	E.P. EERNISSE ET AL., ROLE OF INTEGRATED LATERAL STRESS IN SURFACE DEFORMATION OF H-IMPLANTED SURFACES, 1976, PAGES 9-17
	J.H. EVANS, AN INTERBUBBLE FRACTURE MECHANISM OF BLISTER FORMATION ON HELIUM-IRRADIATED METALS, 1977, PAGES 129-140
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	H.C. SNYMAN ET AL, TRANSMISSION ELECTRON MICROSCOPY OF EXTENDED CRYSTAL DEFECTS IN PROTON BOMBARDED AND ANNEALED GaAs, 1982, PAGES 199-230
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*EXAMINER INITIAL	OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)
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	H. MORICEAU ET AL, A NEW CHARACTERIZATION PROCESS USED TO QUALIFY SOI FILMS, 1991 PAGES 173-178
	A.J. AUBERTON-HERVE ET AL., SOI MATERIALS FOR ULSI APPLICATION, 1995,
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Dmc	M. BRUEL ET AL., "SMART-CUT": A PROMISING NEW SOI MATERIAL TECHNOLOGY, 1995, PAGES 178-179
	B. ASPAR ET AL, TRANSFER OF STRUCTURED AND PATTERNED THIN SILICON FILMS USING THE SMART-CUT PROCESS, 1996, PAGES 1985-1986
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	LETI OUTLINE- A NEW SOI MATERIAL TECHNOLOGY, 1996 (AUTHOR UNKNOWN), (PAGES UNKNOWN)
	B. ASPAR, BASIC MECHANISMS INVOLVED IN THE SMART-CUT PROCESS, 1997, PAGES 223-240
	MICHEL BRUEL ET AL, SMART-CUT: A NEW SILICON ON INSULATOR MATERIAL TECHNOLOGY BASED ON HYDROGEN IMPLANTATION AND WAFER BONDING, 1997, PAGES 1636-164, COL. 36, PART 1, NO. 3B
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	CHRISTOPHE MALEVILLE ET AL, WAFER BONDING AND H-IMPLANTATION MECHANISMS INVOLVED IN THE SMART-CUT TECHNOLOGY, 1997, PAGES 14-19
	H. MORICEAU ET AL, THE SMART-CUT PROCESS AS A WAY TO CHIEVE SPECIFIC FILM THICKNESS IN SOI STRUCTURES, 1997, PAGES (UNKNOWN)
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ASPAR ET AL

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GROUP	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	19	20	21	22	23	24	25	26	27	28	29	30	31	32	33	34	35	36	37	38	39	40	41	42	43	44	45	46	47	48	49	50	51	52	53	54	55	56	57	58	59	60	61	62	63	64	65	66	67	68	69	70	71	72	73	74	75	76	77	78	79	80	81	82	83	84	85	86	87	88	89	90	91	92	93	94	95	96	97	98	99	100
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		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO

One		Comparative study of annealed neon-, argon-, and krypton- ion implantation damage in silicon, A.G. Cullis, T. E. Seidel and R.L. Meek, J. Appl. Phys. 49(10) October 1978, pgs. 5188 - 5198
One		Equilibrium Shape of Si, Eaglesham, White, Feldman, Moriya nd Jacobson, Physical Review Letters, Volume 70, Number 11, March 15, 1993, pgs. 1643-1646

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D. M. ZOLDS

DATE CONSIDERED

12-21-05

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APPLICANT(S)

ASPAR ET AL

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Dme		La Formation Des Cloques, Saint-Jacques, Nuclear Instruments and Methods 209/210 (1983), pgs. 333-343
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BREV 12370 CON	777516
APPLICANT(S) ASPAR ET AL	
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<p>one</p>	<p>Helium Bubble and Blister Formation for Nickel and An AMorphous Fe-Ni-Mo-B Alloy During 5 keV He+-Irradiation at Temperatures Between 200 K and 600 K, Swijgenhoven, Stals and Knuyt, Nuclear Instruments and Methods 209/210 (1983) pgs. 461-468</p>
<p>one</p>	<p>Infrared Spectroscopy of chemically bonded hydrogen at voids and defects in silicon, Stein, Myers and Follstaedt, J. Appl. Phys. 73(b6), 15 March 1993, pgs. 2755-2764</p>

D.M. COLLINS

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Dmc		Silicon-on-insulator produced by helium implantation and thermal oxidation, Raineri, Campisano, Appl. Phys. Lett. 66 (26), 26 June 1995, pgs. 3654-3656
Dmc		Radiative Recombination Channels due to Hydrogen in Crystalline Silicon, Canham, Dyball, Leong, Houlton, Cullis and Smith, Nterials Science and Engineering, B4 (1989) pgs 41-45

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FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE
(Modified) PATENT AND TRADEMARK OFFICE

INFORMATION DISCLOSURE
STATEMENT BY APPLICANT

(Use several sheets if necessary)

(37 CFR 1.98(b))

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U.S. PATENT DOCUMENTS

EXAMINER INITIAL	PATENT NUMBER	ISSUE DATE	PATENTEE	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
Dmc	5 3 7 4 5 6 4	12/20/94	Bruehl	437	24	
	5 4 1 3 9 5 1	5/9/95	Ohori et al	437	61	
	5 5 2 4 3 3 9	6/11/96	Gorowitz et al	29	841	
	5 5 5 9 0 4 3	9/24/96	Bruehl	437	24	
	5 5 6 7 6 5 4	10/22/96	Beilstein, Jr. et al	437	209	
	5 6 1 8 7 3 9	4/8/97	Takabashi et al	438	158	
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FOREIGN PATENT OR PUBLISHED FOREIGN PATENT APPLICATION

	DOCUMENT NUMBER	PUBLICATION DATE	COUNTRY OR PATENT OFFICE	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
Dmc	7 0 3 6 0 9 A1	3/27/96	EPO	H01L	21/762		X
	5 3 3 5 5 1 A1	9/15/92	EPO	H01L	21/265		X
	6 6 5 5 8 8 A1	1/24/95	EPO	H01L	21/20		X
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OTHER DOCUMENTS (Including Author, Title, Date**, Relevant Pages, Place of Publication***)

Dmc	"Silicon on insulator Material Technology" Bruehl, M.
	Electronic Letters; 31 (1995) 06 July; No. 14; pgs 1201-1202
Dmc	"Investigation of the Bubble Formation Mechanism in a-Si:H films by Fourier-transform infrared microspectroscopy" Mishima et al
	Japan Allied Physics; 64(8); October 15, 1988; pgs. 3972-3974

EXAMINER

D. M. COUZINS

DATE CONSIDERED

12-21-01

EXAMINER: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.